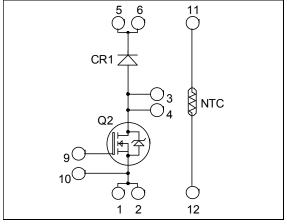
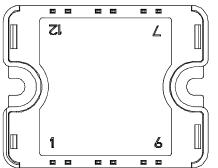


Boost chopper Super Junction MOSFET Power Module





Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		600	V
т	Continuous Drain Current	$T_c = 25^{\circ}C$	95	
ID	Continuous Drain Current	$T_c = 80^{\circ}C$	70	Α
I _{DM}	Pulsed Drain current		260	
V _{GS}	Gate - Source Voltage	±20	V	
R _{DSon}	Drain - Source ON Resistance		24	mΩ
PD	Maximum Power Dissipation	462	W	
I _{AR}	Avalanche current (repetitive and non repetitive)	15	A	
E _{AR}	Repetitive Avalanche Energy	3	mJ	
E _{AS}	Single Pulse Avalanche Energy	1900	IIIJ	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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 $V_{DSS} = 600V$ $R_{DSon} = 24m\Omega \text{ max} @ Tj = 25^{\circ}C$ $I_D = 95A @ Tc = 25^{\circ}C$

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- COOLMOS
 Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electri	Electrical Characteristics							
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$	$T_j = 25^{\circ}C$			350		
		$V_{GS} = 0V, V_{DS} = 600V$	$T_{j} = 125^{\circ}C$			600	μA	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 47.5A$	L			24	mΩ	
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$		2.1	3	3.9	V	
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	V			200	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V; V_{DS} = 25V$		14.4		nF
C _{oss}	Output Capacitance	f = 1 MHz		17		m
Qg	Total gate Charge	$V_{GS} = 10V$		300		
Q _{gs}	Gate – Source Charge	$V_{Bus} = 300 V$		68		nC
Q_{gd}	Gate – Drain Charge	$I_D = 95A$		102		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C)		21		
Tr	Rise Time	$V_{GS} = 10V$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400V$ $I_D = 95A$		100		ns
$T_{\rm f}$	Fall Time	$R_G = 2.5\Omega$		45		
Eon	Turn-on Switching Energy	Inductive switching @ $25^{\circ}C$		1350		μJ
E _{off}	Turn-off Switching Energy	$V_{GS} = 10V$; $V_{Bus} = 400V$ $I_D = 95A$; $R_G = 2.5\Omega$		1040		μι
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 10V$; $V_{Bus} = 400V$		2200		
E _{off}	Turn-off Switching Energy	$V_{GS} = 10V$, $V_{Bus} = 400V$ $I_D = 95A$; $R_G = 2.5\Omega$		1270		μJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			100 500	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		100		А
		$I_F = 100A$			1.6	2	
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 200 {\rm A}$	1		2		V
		$I_{\rm F} = 100 {\rm A}$	$T_i = 125^{\circ}C$		1.3		
t	Reverse Recovery Time	$I_F = 100A$ $V_R = 400V$	$T_j = 25^{\circ}C$		160		ns
t _{rr}			$T_j = 125^{\circ}C$		220		115
Qrr	Reverse Recovery Charge	$v_R = 400 v$ di/dt =200A/µs	$T_j = 25^{\circ}C$		290		nC
			$T_{j} = 125^{\circ}C$		1530		ш



Thermal and package characteristics

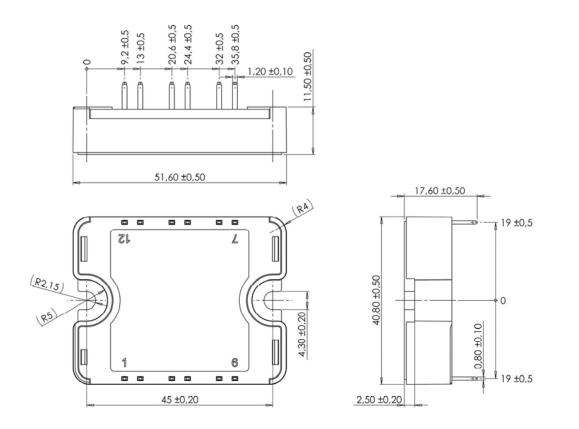
Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance Transistor Diode	tor			0.27	°C/W	
		Diode				0.55	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz						V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
	_				

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



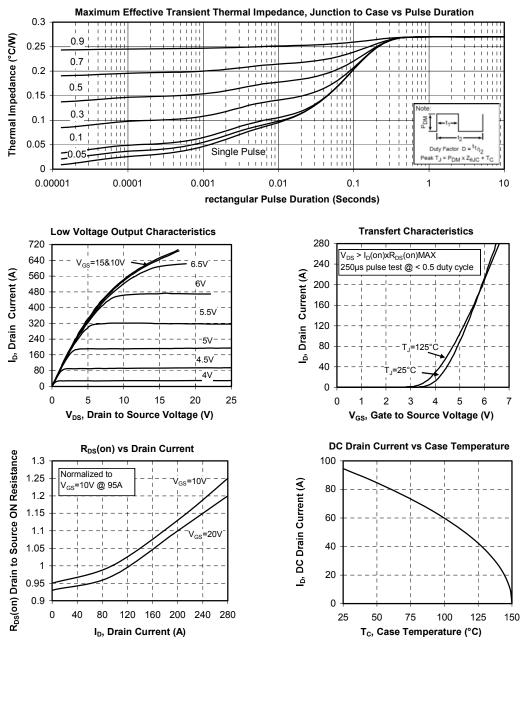
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

www.microsemi.com

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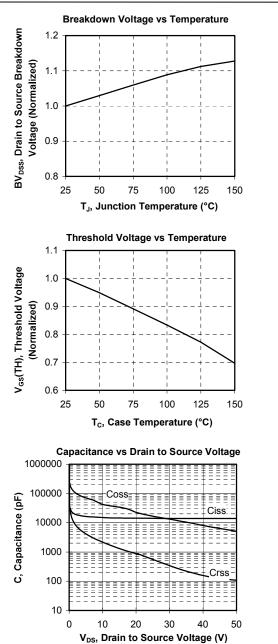


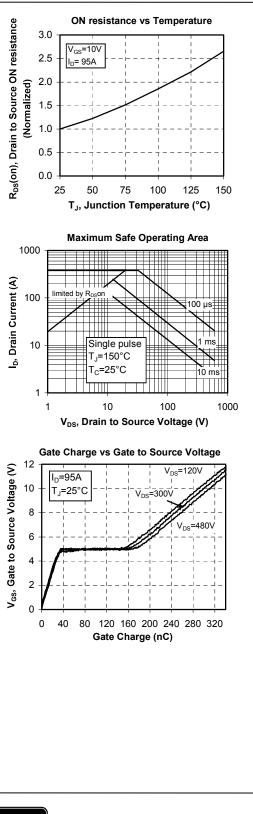
Typical Performance Curve



www.microsemi.com

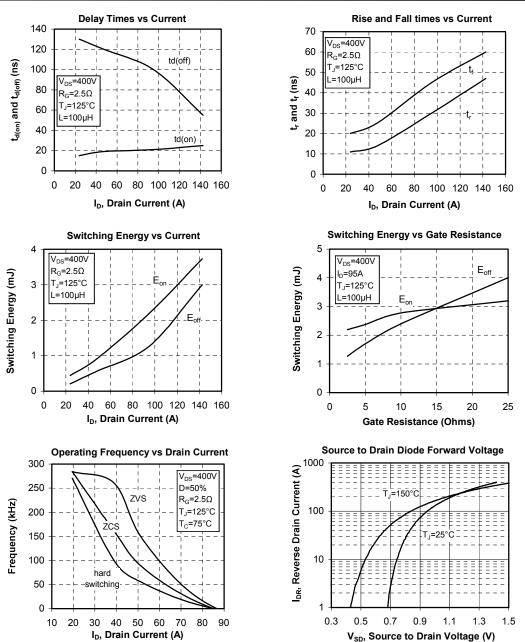






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